

# PJQ4427DP

## 20V P-Channel Enhancement Mode MOSFET

**Voltage**

**-20 V**

**Current**

**-70A**

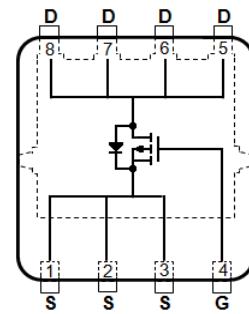
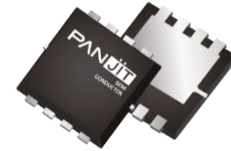
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-8A < 7m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-2.5V$ ,  $I_D@-5A < 10m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-1.8V$ ,  $I_D@-3A < 15m\Omega$
- LOW  $R_{DS(ON)}$
- High current rating
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

DFN3333-8L



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	-20	V
Gate-Source Voltage		$V_{GS}$	$\pm 10$	
Continuous Drain Current <sup>(Note 4)</sup>	$T_A=25^\circ C$	$I_D$	-16	A
	$T_A=70^\circ C$		-13	
Pulsed Drain Current <sup>(Note 1)</sup>	$T_A=25^\circ C$	$I_{DM}$	-120	
Power Dissipation	$T_A=25^\circ C$	$P_D$	2.8	W
	$T_A=70^\circ C$		1.8	
Continuous Drain Current <sup>(Note 4)</sup>	$T_C=25^\circ C$	$I_D$	-70	A
	$T_C=100^\circ C$		-44	
Power Dissipation	$T_C=25^\circ C$	$P_D$	50	W
	$T_C=100^\circ C$		20	
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		$E_{AS}$	56	mJ
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	$^\circ C$
Typical Thermal Resistance <sup>(Note 5)</sup>	Junction to Case	$R_{\theta JC}$	2.5	$^\circ C/W$
	Junction to Ambient	$R_{\theta JA}$	45	

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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.5	-0.68	-1.1	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-8A	-	5.8	7	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-5A	-	7.4	10	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-3A	-	10.6	15	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>Dynamic</b> (Note 7)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-8A, V <sub>GS</sub> =-4.5V (Note 2,3)	-	45	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	5	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	11	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHZ	-	4389	-	pF
Output Capacitance	C <sub>oss</sub>		-	360	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	270	-	
Gate resistance	R <sub>g</sub>	f=1MHZ	-	5.5	-	Ω
Turn-On Delay Time	td(on)	V <sub>DD</sub> =-10V, I <sub>D</sub> =-8A, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =25Ω (Note 2,3)	-	38	-	ns
Turn-On Rise Time	tr		-	147	-	
Turn-Off Delay Time	td(off)		-	382	-	
Turn-Off Fall Time	tf		-	224	-	
<b>Drain-Source Diode</b>						
Diode Forward Current	I <sub>s</sub>	---	-	-	-70	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.6	-1.0	V
Reverse Recovery Time	T <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-8A	-	17.6	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>	dI <sub>S</sub> /dt=100A/us	-	4.1	-	nC

Notes :

1. Pulse width < 300us, Duty cycle < 2%.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T<sub>J</sub>(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> = 25°C.
4. The maximum current rating is package limited.
5. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz. square pad of copper.
6. The test condition is L=0.1mH, I<sub>AS</sub>=-33A, V<sub>DD</sub>=-15V, R<sub>G</sub>=25 ohm, Starting T<sub>J</sub>=25°C.
7. Guaranteed by design, not subject to production testing.

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## TYPICAL CHARACTERISTIC CURVES

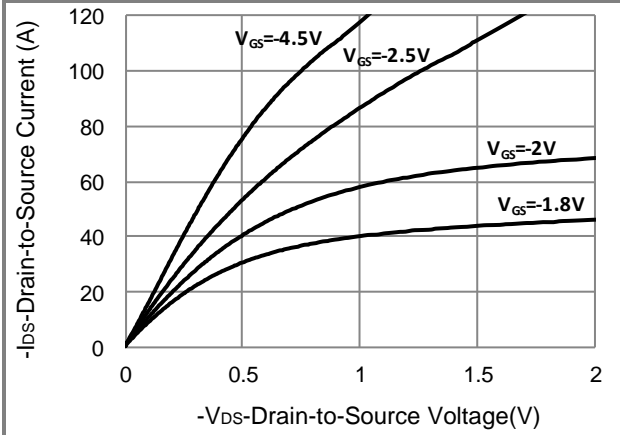


Fig.1 Output Characteristics

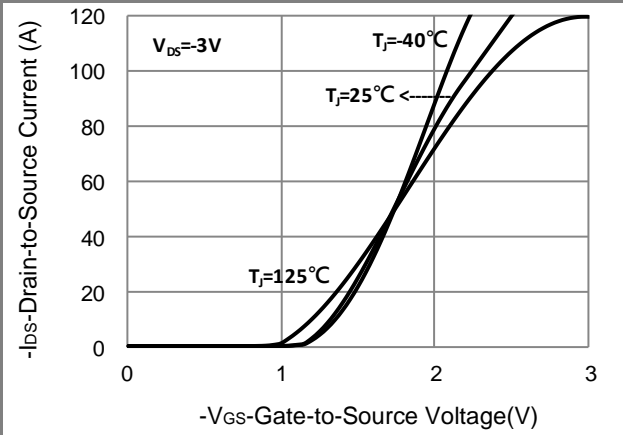


Fig.2 Transfer Characteristics

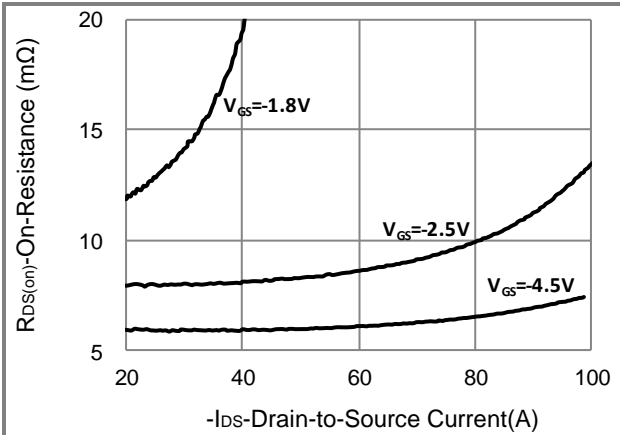


Fig.3 On-Resistance vs. Drain Current

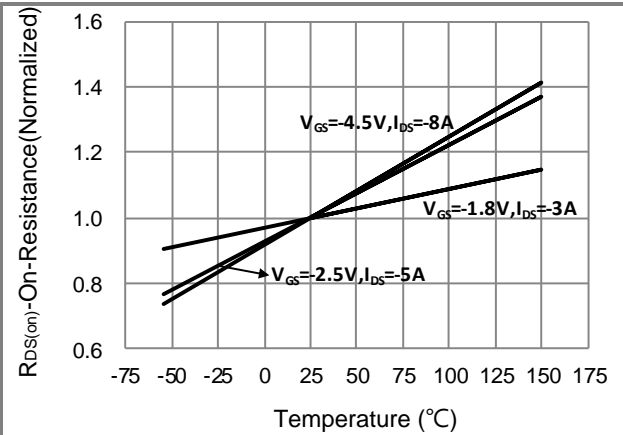


Fig.4 On-Resistance vs. Junction temperature

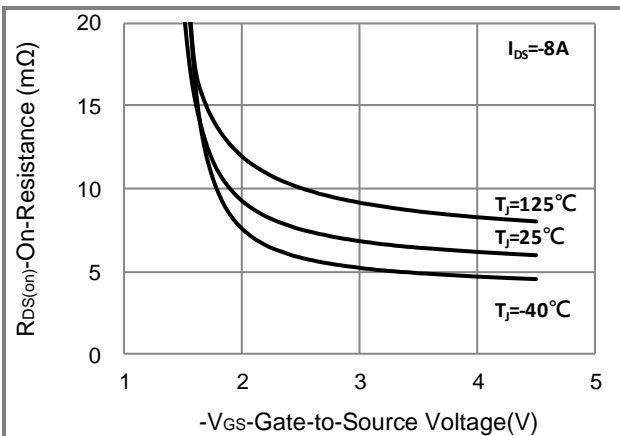


Fig.5 On-Resistance Variation with  $V_{GS}$

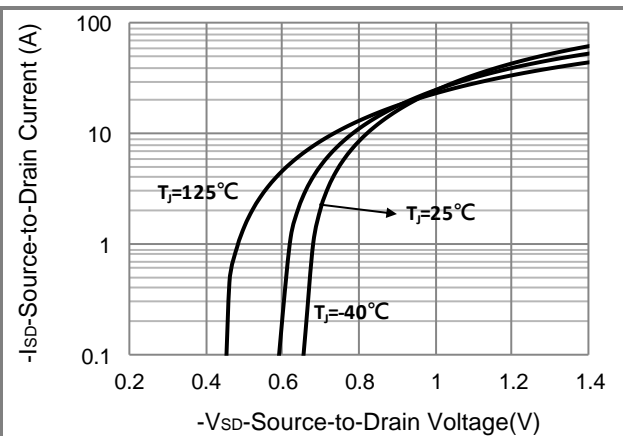


Fig.6 Source-Drain Diode Forward Voltage

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## TYPICAL CHARACTERISTIC CURVES

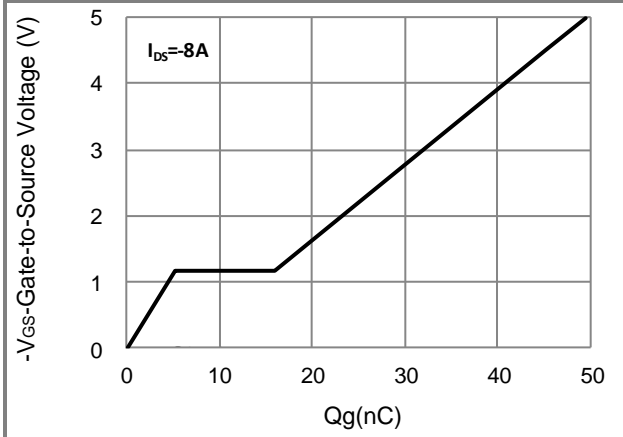


Fig.7 Gate-Charge Characteristics

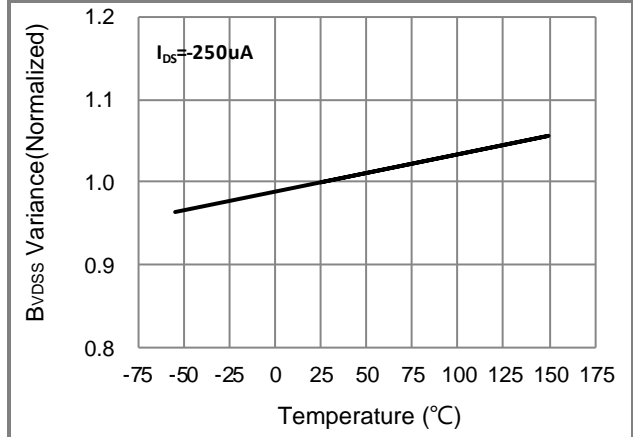


Fig.8 Breakdown Voltage Variation vs. Temperature

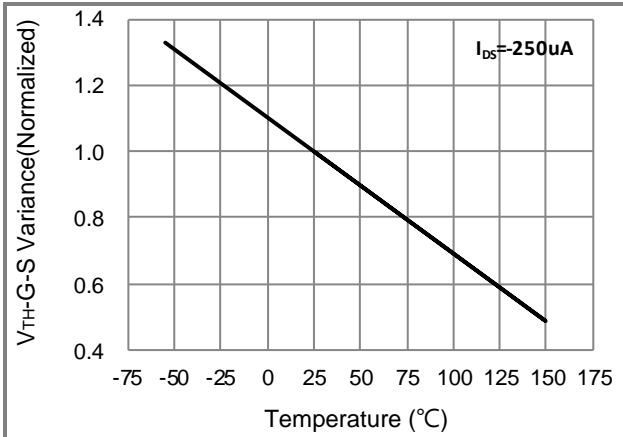


Fig.9 Threshold Voltage Variation with Temperature

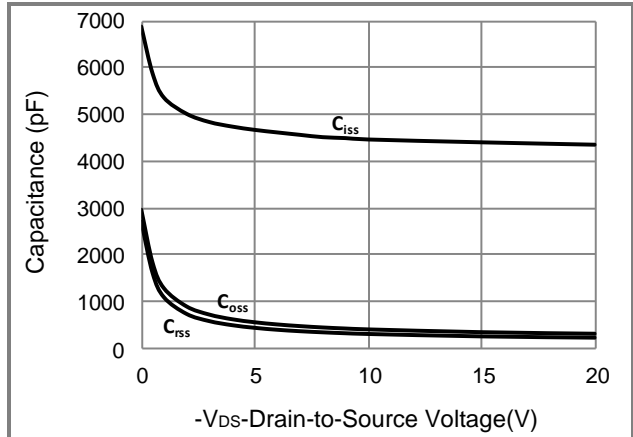


Fig.10 Capacitance vs. Drain-Source Voltage

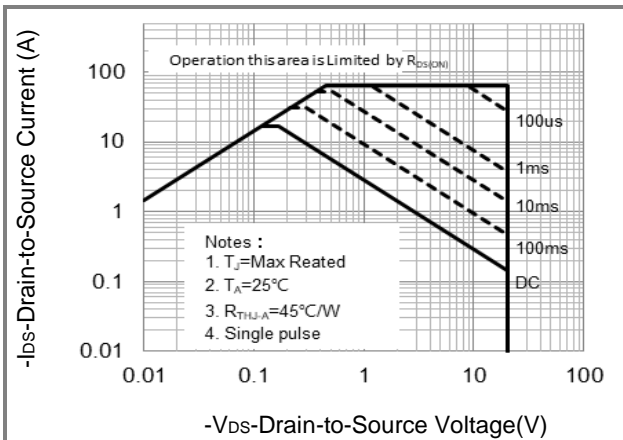


Fig.11 Maximum Safe Operating Area

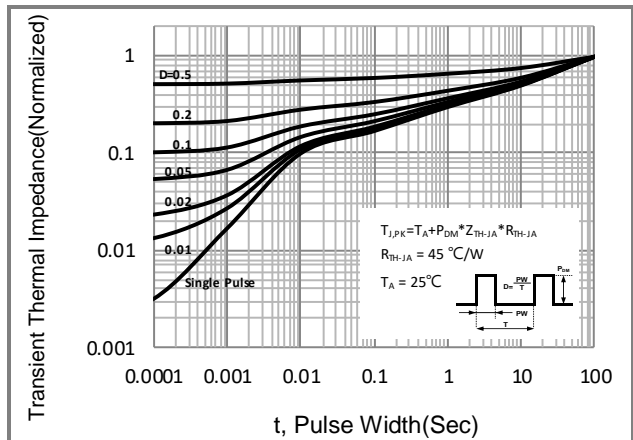
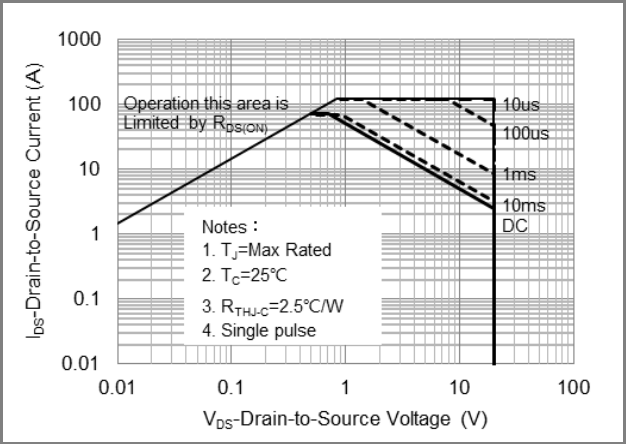


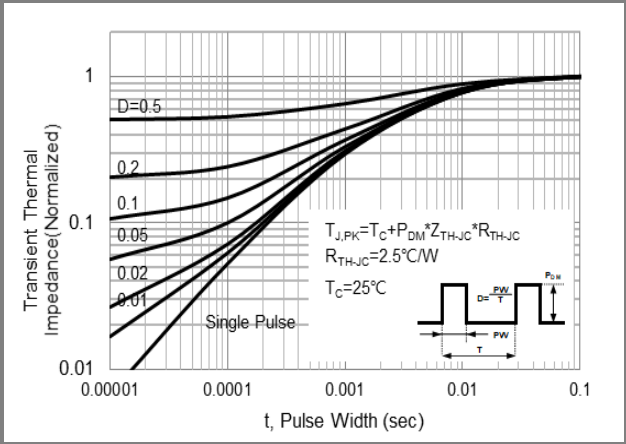
Fig.12 Normalized Transient Thermal Impedance

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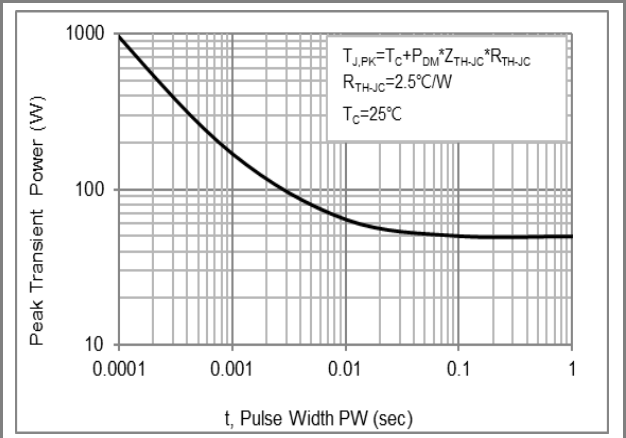
## TYPICAL CHARACTERISTIC CURVES



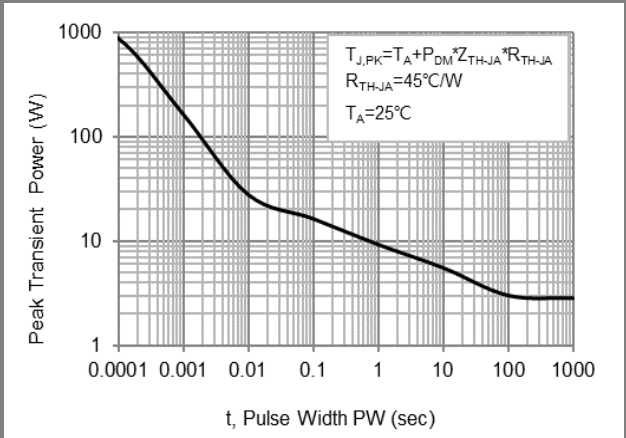
**Fig.13 Maximum Safe Operating Area**



**Fig.14 Normalized Transient Thermal Impedance**



**Fig.15 Single Pulse Maximum Power Dissipation**



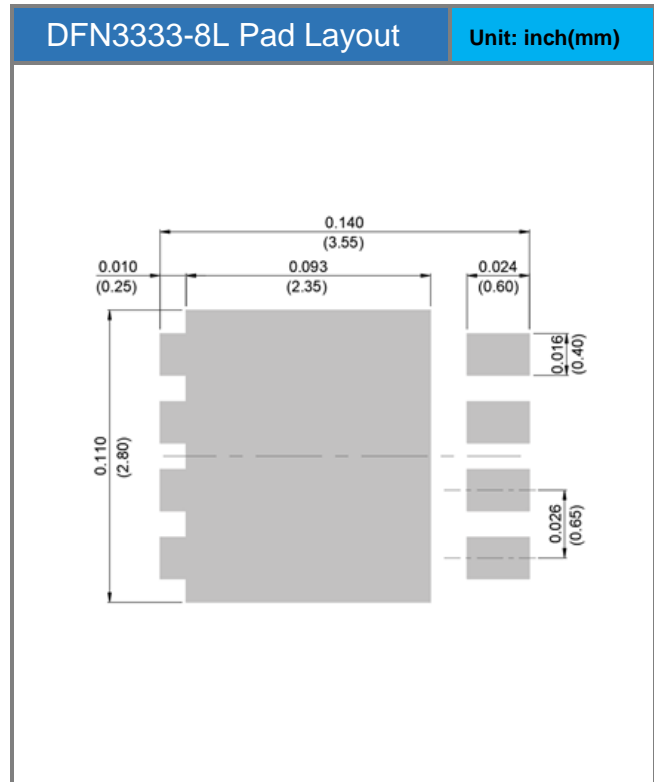
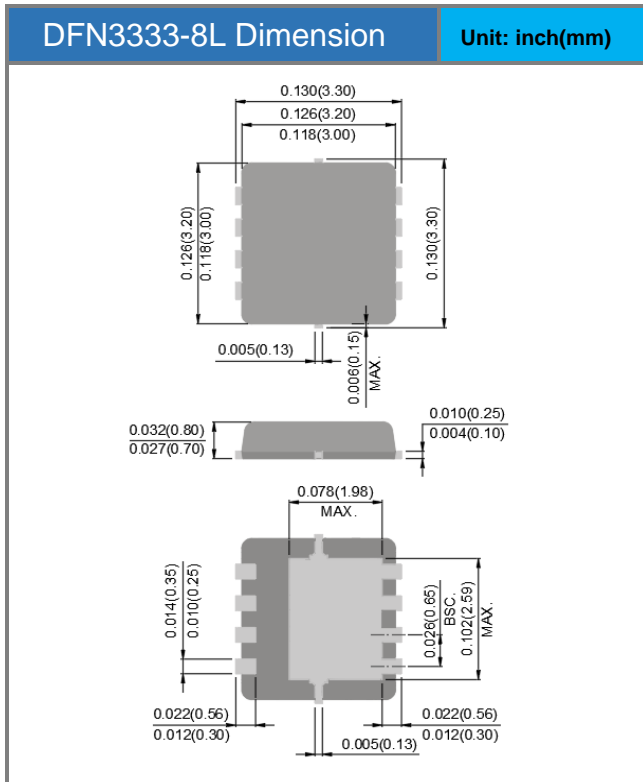
**Fig.16 Single Pulse Maximum Power Dissipation**

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## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ4427DP	DFN3333-8L	5K pcs / 13" reel	4427

## Packaging Information & Mounting Pad Layout



## PJQ4427DP

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